

Features

- Uses BeST advanced Trench MOS technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \cdot R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Applications

- Motor control and drive
- Battery management
- UPS

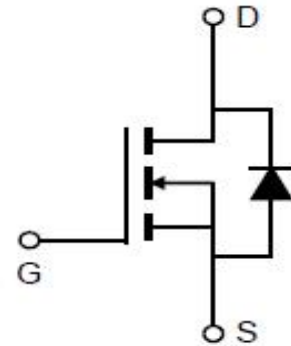
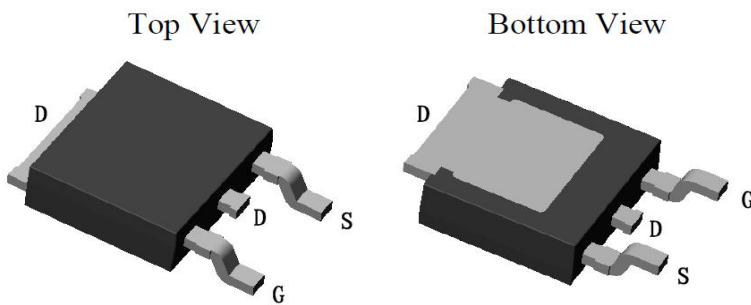
Product Summary

V_{DS}	30V
$R_{DS(on)}$ typ.	3.1mΩ
I_D	80A

100% DVDS Tested

100% Avalanche Tested

TO-252



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
BST045N03DL	BST045N03DL	TO-252	Reel	N/A	N/A	2500pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	30	V
Continuous drain current	I_D	115	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		80	
$T_C = 25^\circ\text{C}$ (Package limit)		72	
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	I_D pulse	320	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	EAS	90	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	101	W
Operating junction and storage temperature	T_j, T_{stg}	-55~150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	1.24	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	94	

Electrical Characteristic (at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	30	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	1.3	1.8	2.3	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.02	1	μA	$V_{DS}=30V, V_{GS}=0V$ $T_j=25^\circ C$
		-	-	10		$T_j=125^\circ C$
Gate-source leakage current	I_{GSS}	-	5	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	3.1	4.5	mΩ	$V_{GS}=10V, I_D=30A,$ $T_j=25^\circ C$
		-	5.2	6.5		$T_j=150^\circ C$
		-	4.7	6.5		$V_{GS}=4.5V, I_D=15A,$
Transconductance	g_{fs}	-	73	-	S	$V_{DS}=5V, I_D=30A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	2343	-	pF	$V_{GS}=0V, V_{DS}=30V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	467	-		
Reverse Transfer Capacitance	C_{rss}	-	300	-		
Gate Total Charge	Q_G	-	50	-	nC	$V_{GS}=10V, V_{DS}=15V,$ $I_D=30A, f=1MHz$
Gate-Source charge	Q_{gs}	-	9.5	-		
Gate-Drain charge	Q_{gd}	-	13.5	-		
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{GS}=10V, V_{DD}=15V,$ $R_{G_ext}=3\Omega, I_D=30A,$
Rise time	t_r	-	104	-		
Turn-off delay time	$t_{d(off)}$	-	35	-		
Fall time	t_f	-	94	-		
Gate resistance	R_G	-	1.4	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V _{SD}	-	0.8	1.3	V	V _{GS} =0V, I _{SD} =20A
Body Diode Reverse Recovery Time	t _{rr}	-	22	-	ns	I _F =30A, di/dt=100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	-	12	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

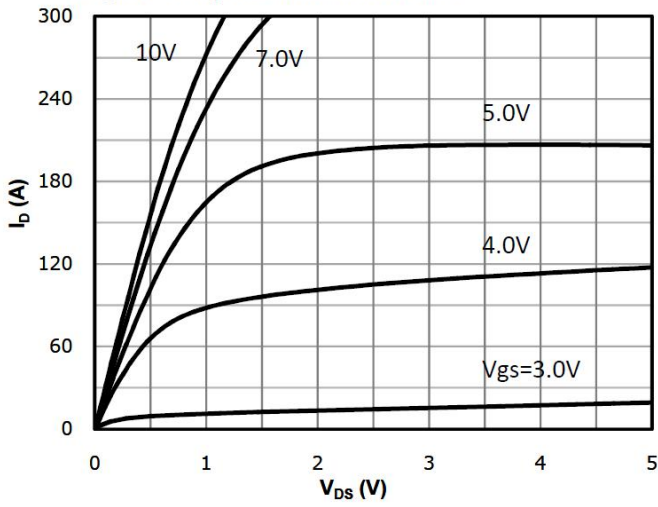


Fig 2: Transfer Characteristics

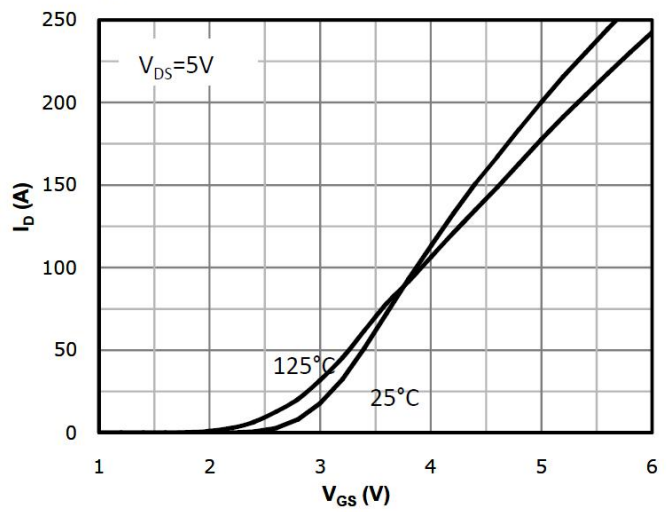


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

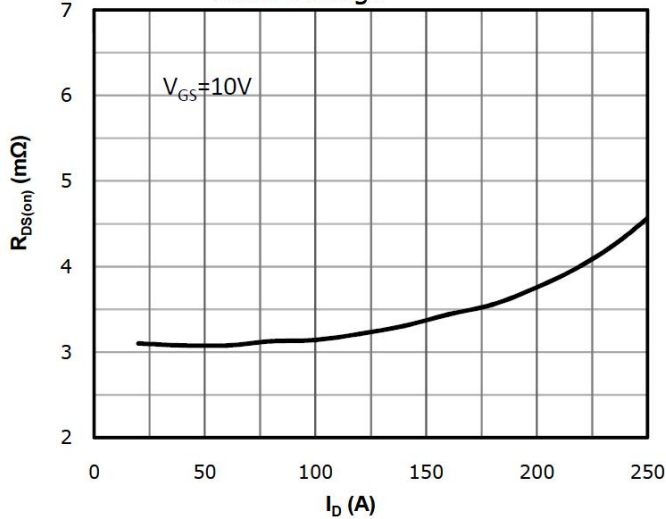


Fig 4: $R_{DS(on)}$ vs Gate Voltage

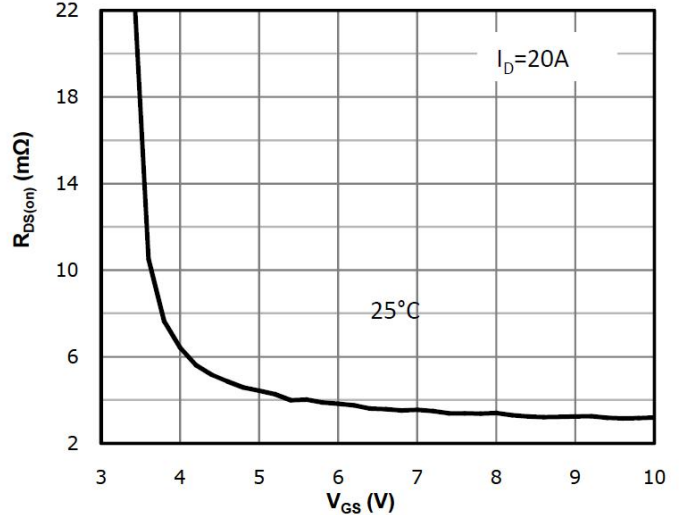


Fig 5: $R_{DS(on)}$ vs. Temperature

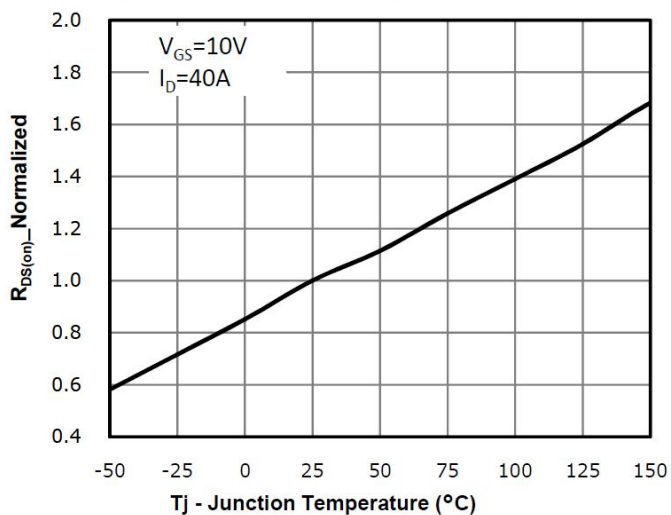


Fig 6: Capacitance Characteristics

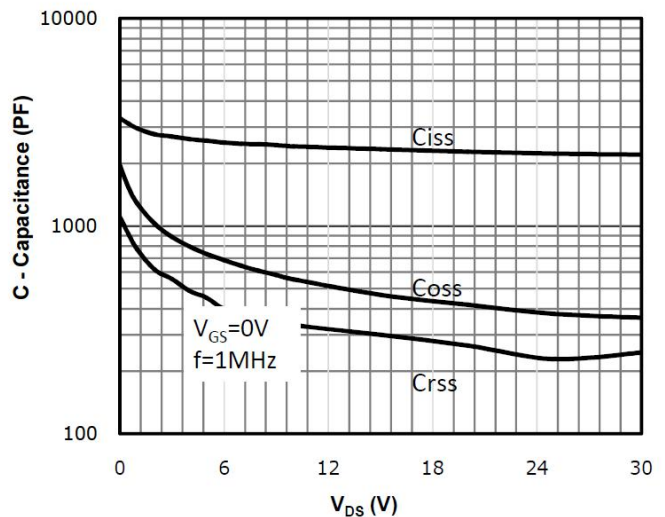


Fig 7: Gate Charge Characteristics

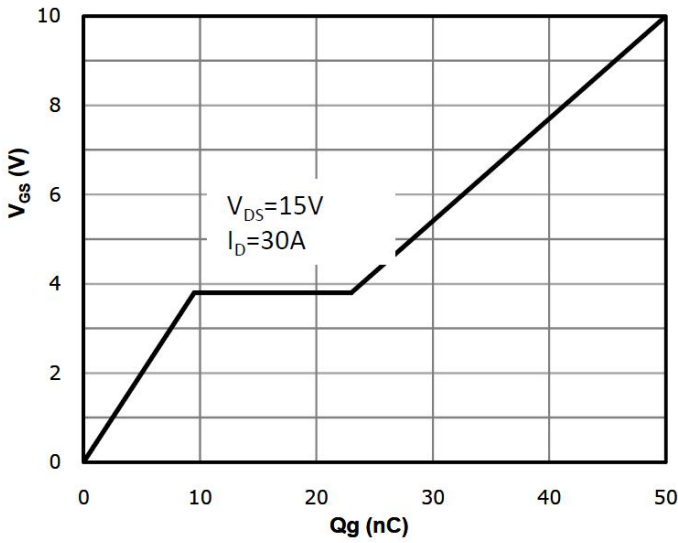


Fig 8: Body-diode Forward Characteristics

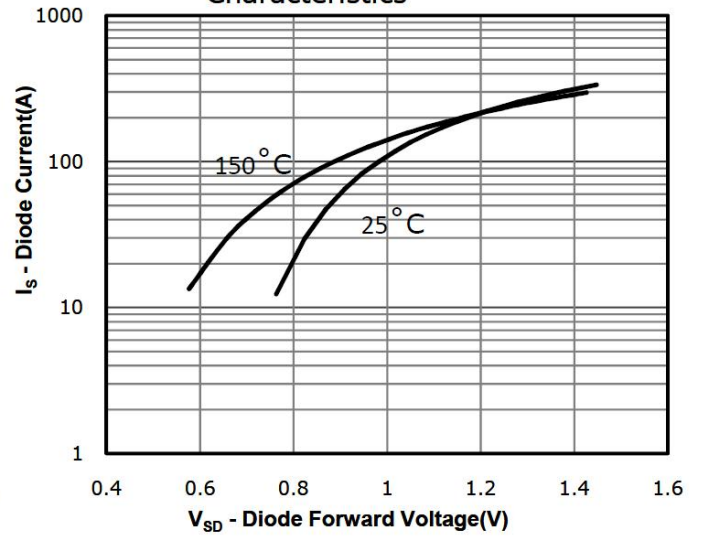


Fig 9: Power Dissipation

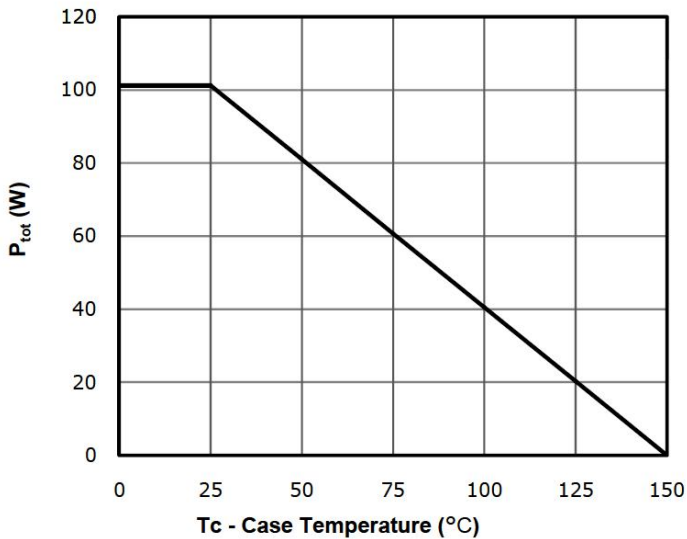


Fig 10: Drain Current Derating

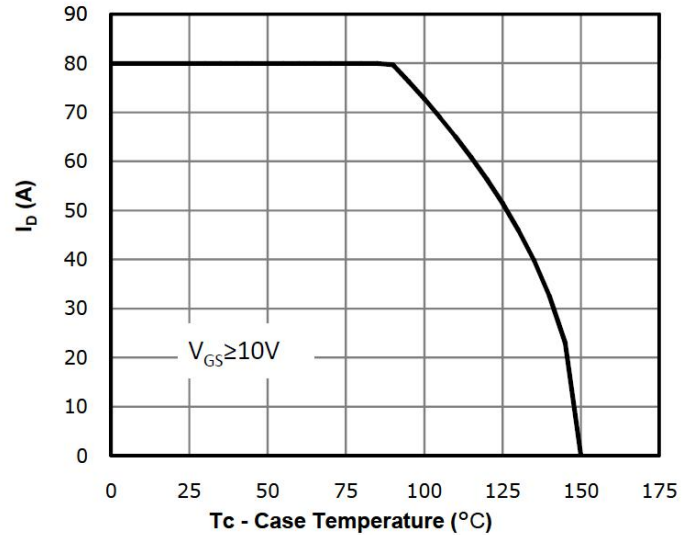


Fig 11: Safe Operating Area

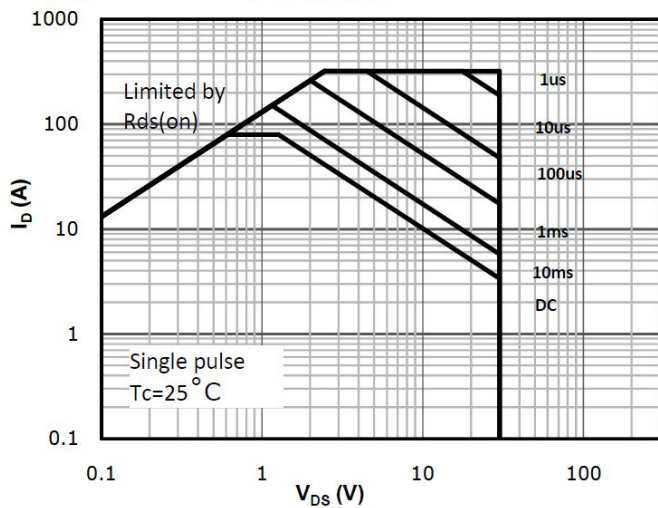
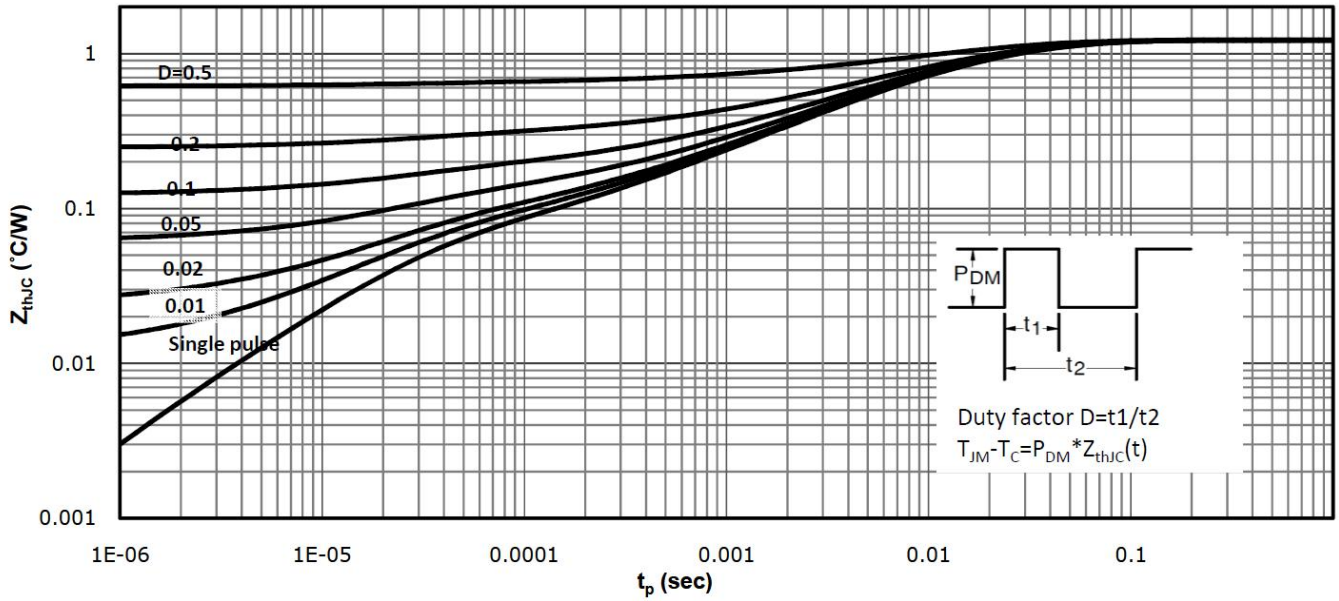
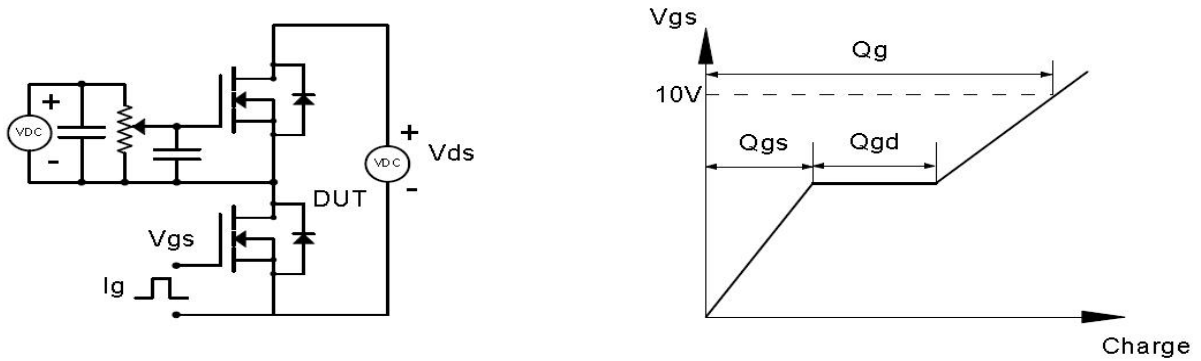


Fig 12: Max. Transient Thermal Impedance

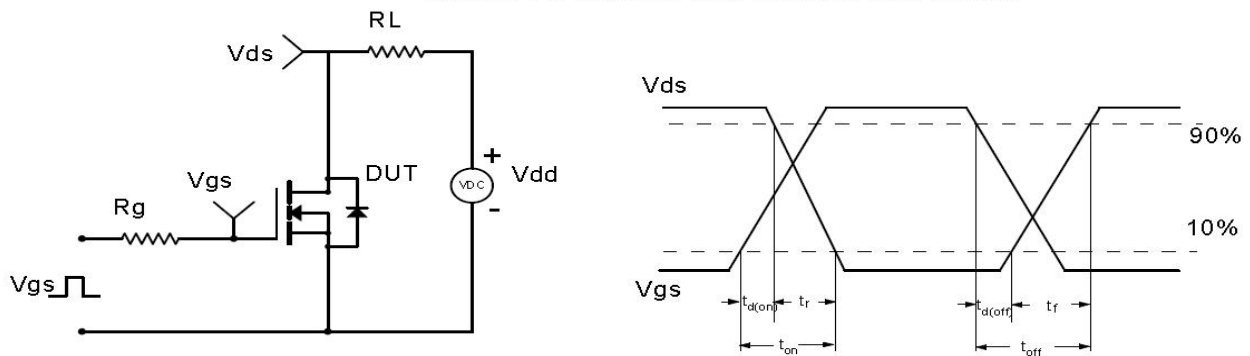


Test Circuit & Waveform

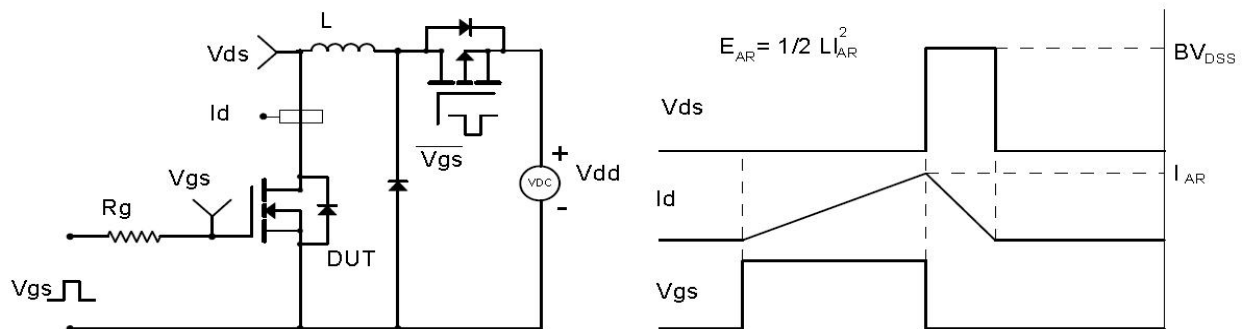
Gate Charge Test Circuit & Waveform



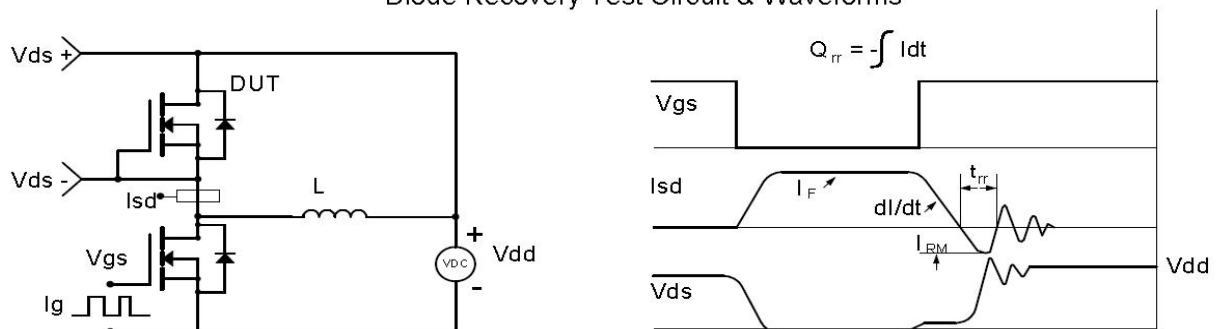
Resistive Switching Test Circuit & Waveforms



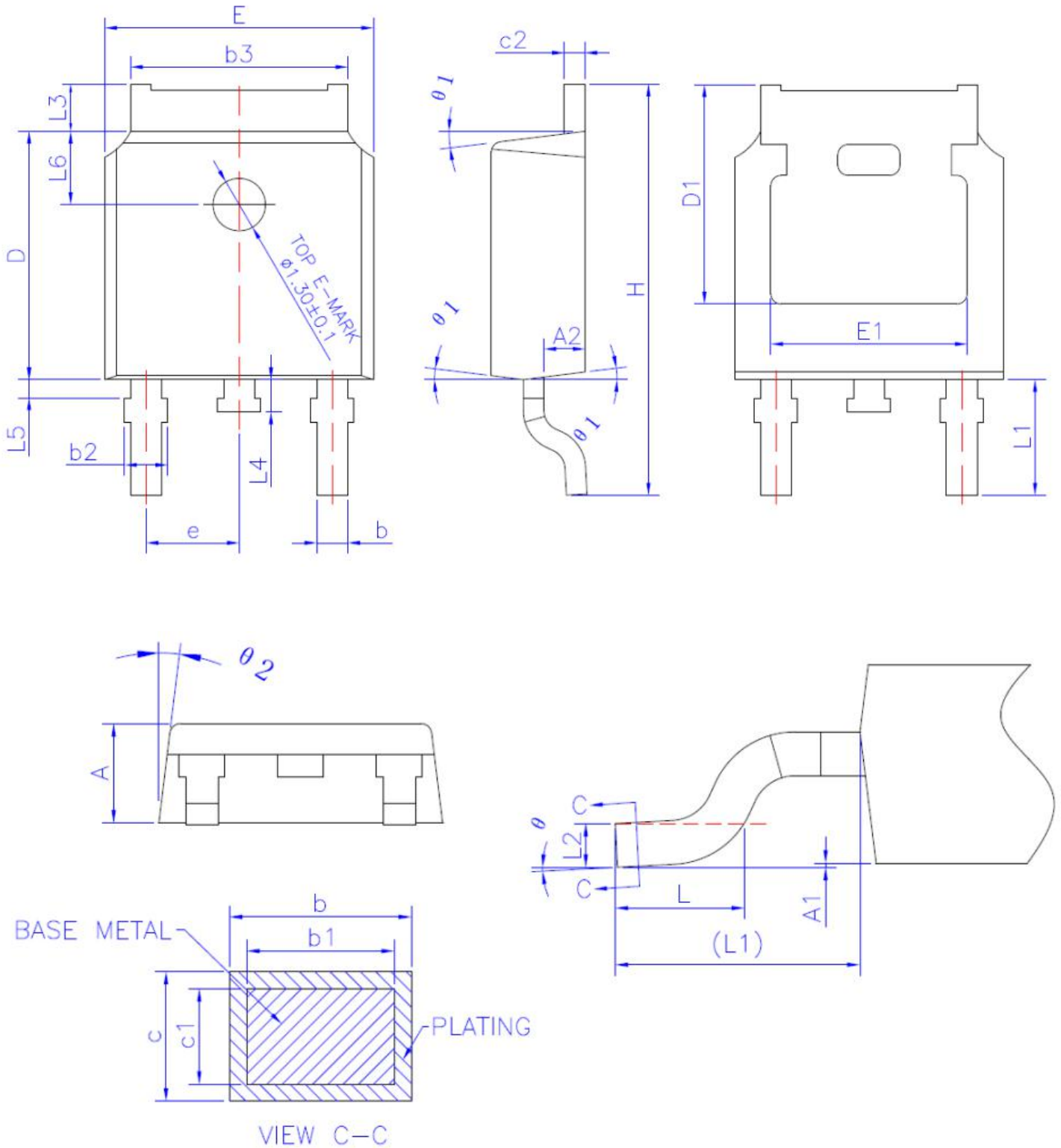
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-252-2



COMMON DIMENSIONS			
UNITS OF MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b1	0.71	0.76	0.81
b2	0.72	-	0.90
b3	5.13	5.33	5.46
c	0.47	-	0.60
c1	0.46	0.51	0.56
c2	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25	-	-
E	6.50	6.60	6.70
E1	4.70	-	-
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.508 BSC		
L3	0.90	-	1.25
L4	0.60	0.80	1.00
L5	0.15	-	0.75
L6	1.80 REF		
θ	0°	-	8°
θ1	5°	7°	9°
θ2	5°	7°	9°

Revision History

Revision	Date	Major changes
1.0	2019/1/24	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

BeST reserves the right to improve product design, function and reliability without notice.